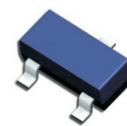


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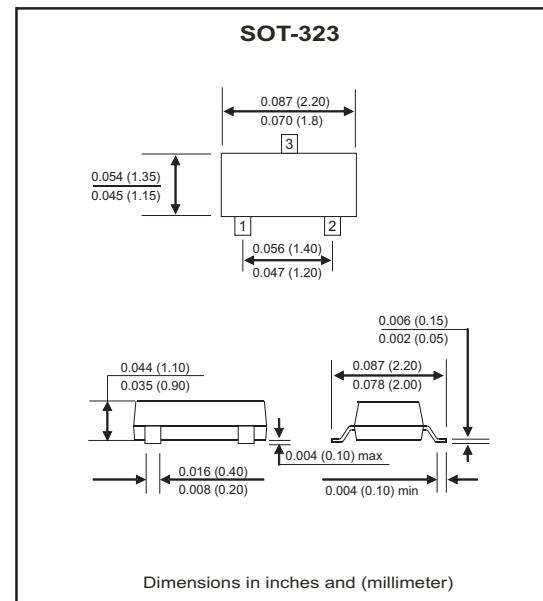
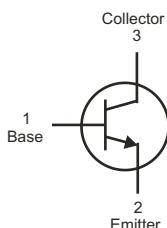
## MMST2222A-G (NPN) RoHS Device



### Features

- Power dissipation  
 $P_{CM}$  : 0.2W ( $T_A=25$  °C)
- Collector current  
 $I_{CM}$  : 0.6A
- Collector-base voltage  
 $V_{(BR)CBO}$  : 75V
- Operating and storage junction temperature range  
 $T_J, T_{STG}$  : -55 °C to +150 °C

### Marking: K3P



### Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Collector-Base breakdown voltage	$I_C = 10\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	75		V
Collector-Emitter breakdown voltage	$I_C = 10\text{mA}, I_B = 0$	$V_{(BR)CEO}$	40		V
Emitter-Base breakdown voltage	$I_E = 10\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	6		V
Collector cut-off current	$V_{CB} = 70\text{V}, I_E = 0$	$I_{CBO}$		0.1	$\mu\text{A}$
Collector cut-off current	$V_{CE} = 35\text{V}, I_B = 0$	$I_{CEO}$		0.1	$\mu\text{A}$
Emitter cut-off current	$V_{EB} = 3\text{V}, I_C = 0$	$I_{EBO}$		0.1	$\mu\text{A}$
DC current gain	$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	$h_{FE}(1)$	100	300	
	$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	$h_{FE}(2)$	50		
Collector-Emitter saturation voltage	$I_C = 500\text{mA}, I_B = 50\text{mA}$	$V_{CE(sat)}$		0.6	V
Base-Emitter saturation voltage	$I_C = 500\text{mA}, I_B = 50\text{mA}$	$V_{BE(sat)}$		1.2	V
Transition frequency	$V_{CE} = 20\text{V}, I_C = 20\text{mA}$ $f = 100\text{MHz}$	$f_T$	300		MHz
Output capacitance	$V_{CB} = 10\text{V}, I_E = 0$ $f = 1\text{MHz}$	$C_{ob}$		8	pF
Delay time	$V_{CC} = 30\text{V}, I_C = 150\text{mA}$ $V_{BE(off)} = 0.5\text{V}, I_B1 = 15\text{mA}$	$t_d$		10	nS
Rise time		$t_r$		25	nS
Storage time	$V_{CC} = 30\text{V}, I_C = 150\text{mA}$ $I_B1 = I_B2 = 15\text{mA}$	$t_s$		225	nS
Fall time		$t_f$		60	nS

REV:A

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## RATING AND CHARACTERISTIC CURVES (MMST2222A-G)

Fig.1 Grounded Emitter Output Characteristics

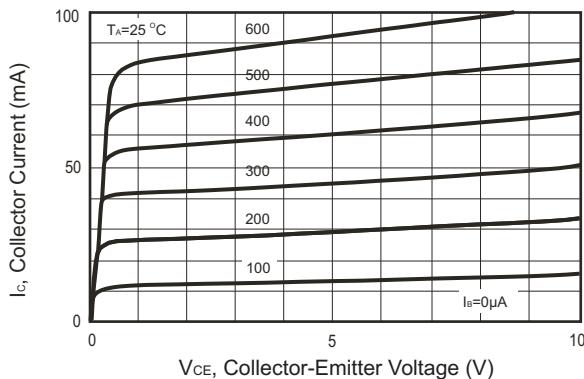


Fig.2 Collector-Emitter Saturation Voltage vs. Collector Current

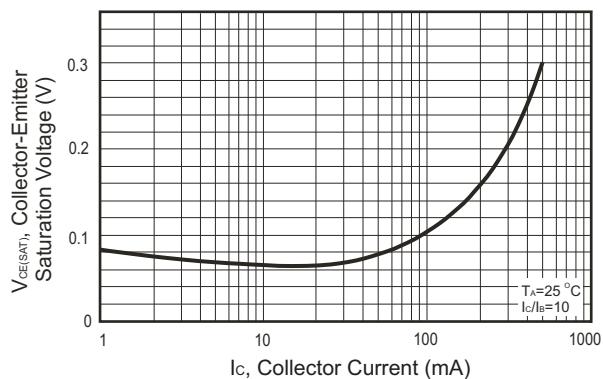


Fig.3 DC Current Gain vs. Collector Current

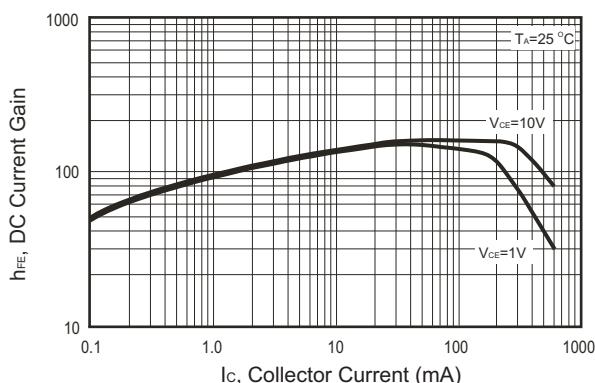


Fig.4 DC Current Gain vs. Collector Current

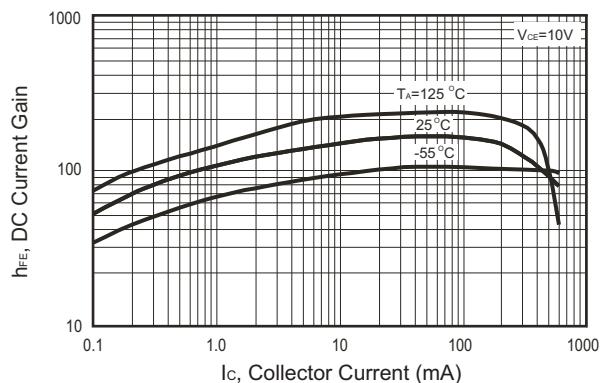


Fig.5 AC Current gain vs. Collector Current

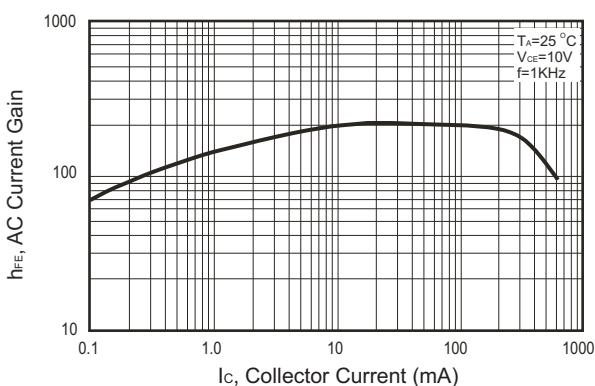
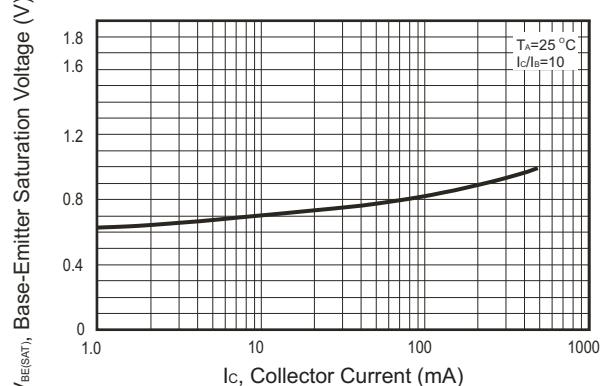


Fig.6 Base-Emitter Saturation Voltage vs. Collector Current



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## RATING AND CHARACTERISTIC CURVES (MMST2222A-G)

Fig.7 Grounded-Emitter Propagation Characteristics

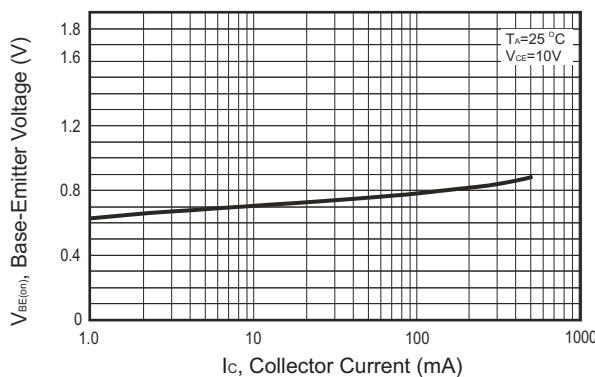


Fig.8 Turn-on time vs. Collector Current

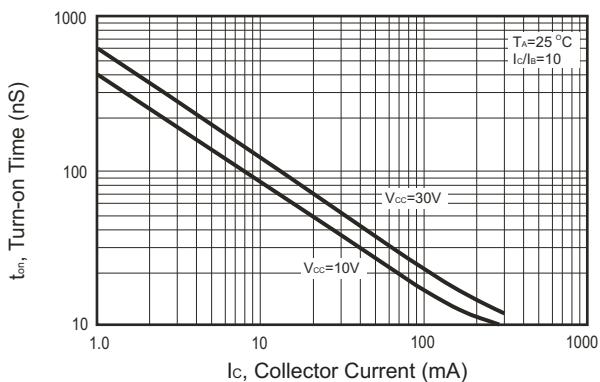


Fig.9 Rise Time vs. Collector Current

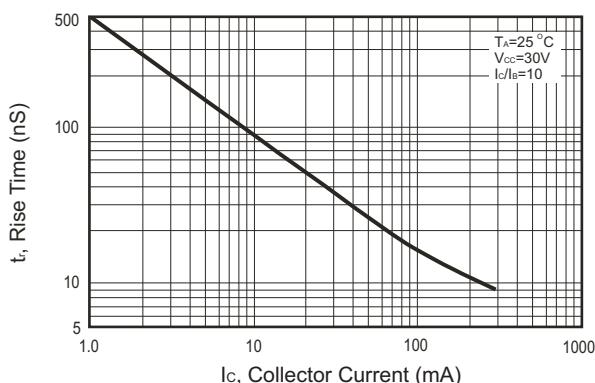


Fig.10 Storage Time vs. Collector Current

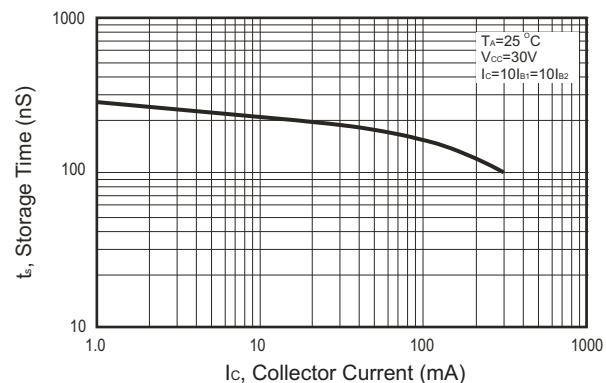


Fig.11 Fall Time vs. Collector Current

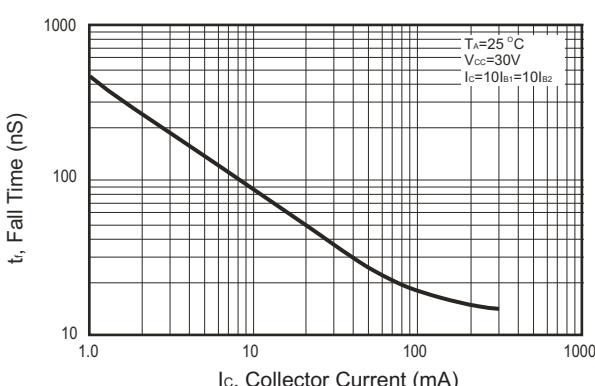
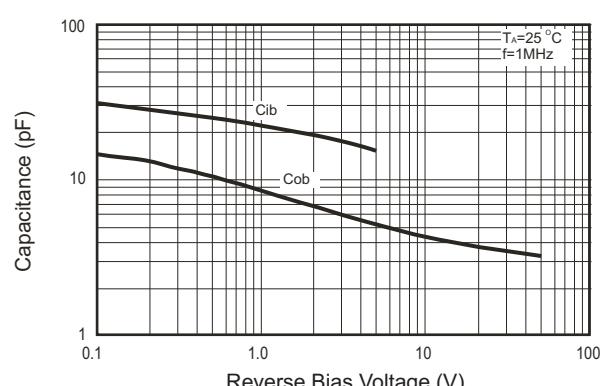


Fig.12 Input/Output Capacitance vs. Voltage



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## RATING AND CHARACTERISTIC CURVES (MMST2222A-G)

Fig.13 Gain Bandwidth Product

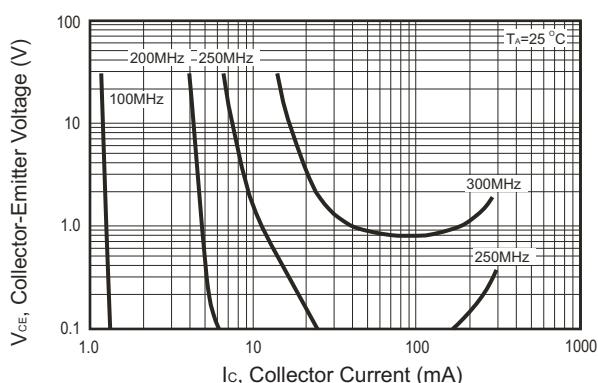


Fig.14 Gain Bandwidth product  
vs. Collector Current

